What is claimed is:

1. (Original) An antifuse structure comprising:

a fin having a center portion and end portions,

wherein said center portion of said fin comprises a substantially non-conductive region adapted to permanently become a conductor when heated above a predetermined temperature,

wherein said end portions comprise conductors.

2. (Original) The antifuse in claim 1, wherein said center portion of said fin comprises an amorphous material.

3. (Original) The antifuse in claim 1, wherein said center portion of said fin is approximately 10 times more conductive after being heated above said predetermined temperature when compared to a conductivity level of said center portion before heating.

4. (Original) The antifuse in claim 1, wherein said center portion comprises less than approximately 10 percent of the length of said fin.

5. (Original) The antifuse in claim 1, wherein said center portion comprises amorphous silicon before being heated above said predetermined temperature and comprises polycrystalline silicon after being heated above said predetermined temperature.

6. (Currently Amended) The antifuse in claim 1, wherein said end portions comprise silicide regions of said ~~fins~~ fin.

7. (Original) The antifuse in claim 1, wherein said fin has a height and length that exceeds more than 2 times a width of said fin.

8-26. (Cancelled).

27. (New) An antifuse structure comprising:

a fin having a center portion and end portions, wherein said fin has a height and length that exceeds a width of said fin,

wherein said center portion of said fin comprises a substantially non-conductive region adapted to permanently become a conductor when heated above a predetermined temperature, and

wherein said end portions comprise conductors.

28. (New) The antifuse in claim 27, wherein said center portion of said fin comprises an amorphous material.

29. (New) The antifuse in claim 27, wherein said center portion of said fin is approximately 10 times more conductive after being heated above said predetermined temperature when compared to a conductivity level of said center portion before heating.

30. (New) The antifuse in claim 27, wherein said center portion comprises less than approximately 10 percent of the length of said fin.

31. (New) The antifuse in claim 27, wherein said center portion comprises amorphous silicon before being heated above said predetermined temperature and comprises polycrystalline silicon after being heated above said predetermined temperature.

32. (New) The antifuse in claim 27, wherein said end portions comprise silicide regions of said fin.

33. (New) The antifuse in claim 27, wherein said height and said length of said fin exceed

more than 2 times said width of said fin.

34. (New) An antifuse structure comprising:

a fin having a center portion and end portions, wherein said fin has a height and length that exceed more than 2 times a width of said fin,

wherein said center portion of said fin comprises a substantially non-conductive region adapted to permanently become a conductor when heated above a predetermined temperature, and

wherein said end portions comprise conductors.

35. (New) The antifuse in claim 34, wherein said center portion of said fin comprises an amorphous material.

36. (New) The antifuse in claim 34, wherein said center portion of said fin is approximately 10 times more conductive after being heated above said predetermined temperature when compared to a conductivity level of said center portion before heating.

37. (New) The antifuse in claim 34, wherein said center portion comprises less than approximately 10 percent of the length of said fin.

38. (New) The antifuse in claim 34, wherein said center portion comprises amorphous silicon before being heated above said predetermined temperature and comprises polycrystalline silicon after being heated above said predetermined temperature.

39. (New) The antifuse in claim 34, wherein said end portions comprise silicide regions of said fin.